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N-Channel 85 V (D-S) MOSFET

PRODUCT SUMMARY						
V _{DS} (V)	R _{DS(on)} (mΩ)(Typ.)	I _D (A) ^a	Q _g (Typ.)			
85	6 at V _{GS} = 10 V	80	60.5 nC			

TO-220 Pin Configuration



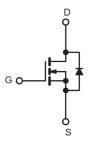
FEATURES

- DT-Trench Power MOSFET
- 100 % R_a and UIS Tested



APPLICATIONS

- · DC/DC converter
- Motor Drives
- · General purposeapplications



N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS (T _A = 25 °C, unless otherwise noted)							
Parameter	Symbol	Limit	Unit				
Drain-Source Voltage		V _{DS}	85	V			
Gate-Source Voltage	V _{GS}	± 20	v				
Continuous Drain Current (T _{.I} = 150 °C)	T _C = 25 °C	I _D	80				
Continuous Brain Current (1) = 100 C)	T _C = 100 °C	טי	60	Α			
Pulsed Drain Current		I _{DM}	320				
Single-Pulse Avalanche Energy	L = 0.5 mH	E _{AS}	505	mJ			
	T _C = 25 °C		184				
Maximum Power Dissipation	T _C = 100 °C	P _D	73.5	w			
Maximum Fower Dissipation	T _A = 25 °C	'D	1.47 ^{b,c}] vv			
	T _A = 100 °C		0.59 ^{b,c}	1			
Operating Junction and Storage Temperature Range		T _J , T _{stg}	- 55 to 150	°C			

THERMAL RESISTANCE RATINGS							
Parameter	Symbol Maximum		Unit				
Maximum Junction-to-Ambient b,d	t ≤ 10 s	R _{thJA}	85	°C/W			
Maximum Junction-to-Case	Steady State	R _{thJC}	0.68	C/VV			

Notes:

- a. Based on T_C = 25 °C.
 b. Surface mounted on 1" x 1" FR4 board.
 c. t = 10 s.
 d. Maximum under steady state conditions is 120 °C/W.



Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit
Static					'	•
Drain-Source Breakdown Voltage	V_{DS}	V _{GS} = 0, I _D = 250 μA	85			V
Gate-Source Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_{D} = 250 \mu\text{A}$	2		4	V
Gate-Source Leakage	I _{GSS}	V _{DS} = 0 V, V _{GS} = ± 20 V			± 100	nA
7 0 1 1/1 5 1 0 1		V _{DS} = 85 V, V _{GS} = 0 V			1	μА
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 70 V, V _{GS} = 0 V, T _J = 55 °C			10	
On-State Drain Current ^a	I _{D(on)}	V _{DS} ≥10 V, V _{GS} = 10 V	80			Α
Drain-Source On-State Resistance ^a	R _{DS(on)}	V _{GS} = 10 V, I _D = 50 A		6	7.2	mΩ
Forward Transconductance ^a	9 _{fs}	V _{DS} = 5 V, I _D = 40 A		72		S
Dynamic ^b						
Input Capacitance	C _{iss}			3120		pF
Output Capacitance	C _{oss}	$V_{DS} = 47.5 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$		460		
Reverse Transfer Capacitance	C _{rss}			17		
Total Gate Charge	Q_g			60.5		nC
Gate-Source Charge	Q _{gs}	$V_{DS} = 47.5 \text{ V}, V_{GS} = 10 \text{ V}, I_{D} = 50 \text{ A}$		10.8		
Gate-Drain Charge	Q _{gd}			18.8		
Gate Resistance	R_g	f = 1 MHz		1.5		Ω
Turn-On Delay Time	t _{d(on)}			18		
Rise Time	t _r	$V_{DD} = 47.5 \text{ V}, R_{L} = 3 \Omega$		35		ns
Turn-Off DelayTime	t _{d(off)}	$I_D \cong 50 \text{ A, V}_{GEN} = 10 \text{ V, R}_g = 1 \Omega$		40		
Fall Time	t _f			19		
Drain-Source Body Diode Characterist	ics					
Continous Source-Drain Diode Current	I _S	T _C = 25 °C			80	Α
Pulse Diode Forward Current (100 μs)	I _{SM}				320	
Body Diode Voltage	V_{SD}	I _S = 1 A			1.2	V
Body Diode Reverse Recovery Time	t _{rr}	I _F = 20 A, dl/dt = 500 A/µs, T ₁ = 25 °C		68		ns
Body Diode Reverse Recovery Charge	Q_{rr}	Q _{rr} 1- 20 A, and - 300 A µ3, 13 - 23 C		66		nC

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

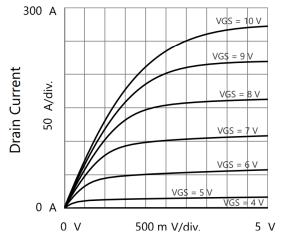
a. Pulse test; pulse width $\leq 300~\mu s,$ duty cycle $\leq 2~\%.$

b. Guaranteed by design, not subject to production testing.

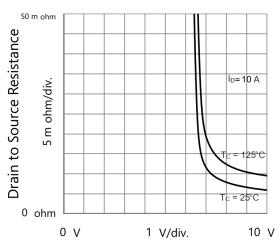




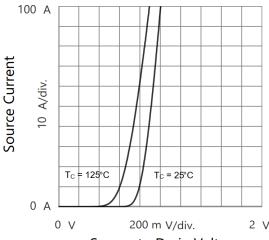
TYPICAL CHARACTERISTICS (25 C, unless otherwise noted)



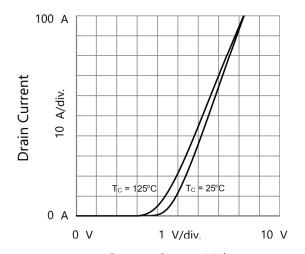
Drain to Source Voltage Output Characteristics



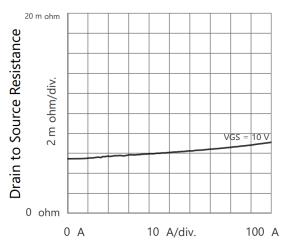
Gate to Source Voltage
Drain to Source Resistance vs. Gate to Source Voltage



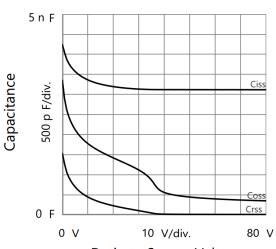
Source to Drain Voltage Body Diode Forward Characteristics



Gate to Source Voltage Transfer Characteristics



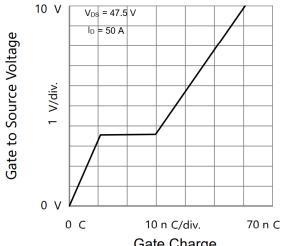
Drain Current
Drain to Source Resistance vs. Drain Current



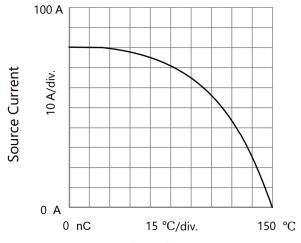
Drain to Source Voltage Capacitances



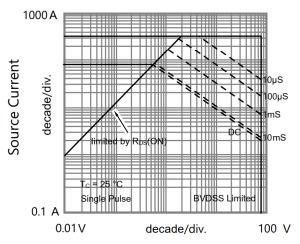
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



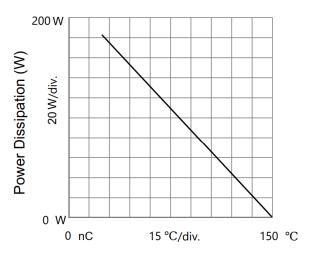
Gate Charge Gate to Source Voltage vs. GateCharge



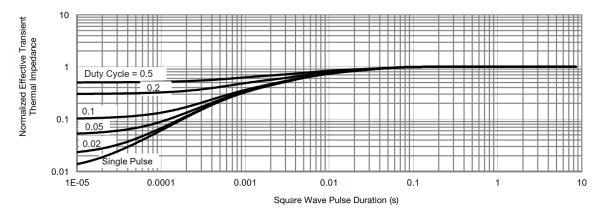
T_C - Case Temperature



Source to Drain Voltage Safe Operating Area, Junction-to-Ambient



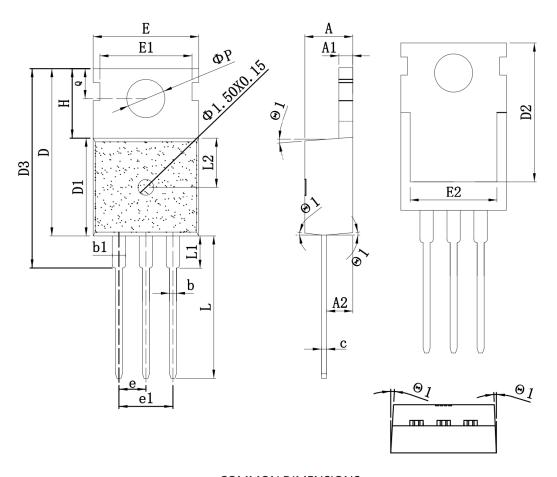
T_C - Case Temperature



Normalized Thermal Transient Impedance, Junction-to-Case



TO-220_3L-A PACKAGE OUTLINE

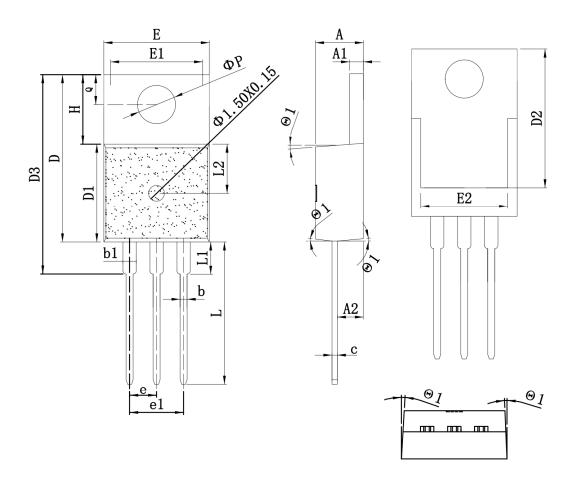


COMMON DIMENSIONS (UNITS OF MEASURE=MILLIMETER)

SYMBOL	mm			SYMBOL	mm		
SIMBOL	MIN	TYP	MAX	SYMBOL	MIN	TYP	MAX
A	4.15	4.50	4.80	E1	8.25	8.70	9.15
A1	1.15	1.30	1.50	E2	7.20	8.00	8.80
A2	2.10	2.40	2.65	e	2.38	2.54	2.74
b	0.65	0.80	1.00	e1	5.08REF		
b1	1.10	1.33	1.80	Н	6.20	6.50	6.90
c	0.35	0.50	0.65	L	12.75	13.28	13.70
D	14.25	15.75	16.15	L1	-	-	3.50
D1	8.70	9.20	9.60	L2	2.30	4.65	7.00
D2	12.30	13.10	13.85	φP	3.40	3.65	3.85
D3	16.20	18.80	20.60	Q	2.50	2.80	3.00
Е	8.68	10.02	11.00	θ	2°	-	7°



TO-220_3L-B PACKAGE OUTLINE



COMMON DIMENSIONS (UNITS OF MEASURE=MILLIMETER)

SYMBOL	mm			CVMDOI	mm		
	MIN	TYP	MAX	SYMBOL	MIN	TYP	MAX
A	4.15	4.50	4.80	E1	8.25	8.70	9.15
A1	1.15	1.30	1.50	E2	7.20	8.00	8.80
A2	2.10	2.40	2.65	e	2.38	2.54	2.74
b	0.65	0.80	1.00	e1	5.08REF		
b1	1.10	1.33	1.80	Н	6.20	6.50	6.90
С	0.35	0.50	0.65	L	12.75	13.28	13.70
D	14.25	15.75	16.15	L1	-	1	3.50
D1	8.70	9.20	9.60	L2	2.30	4.65	7.00
D2	12.30	13.10	13.85	φP	3.40	3.65	3.85
D3	16.20	18.80	20.60	Q	2.50	2.80	3.00
Е	8.68	10.02	11.00	θ	2°	-	7°

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